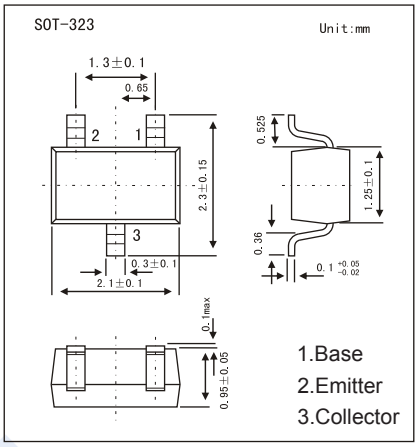
PNP Transistors

MMST5401 (KMST5401)



■ Features

- Small Surface Mount Package
- Ideal for Medium Power Amplificationand Switching
- Complementary to MMST5551

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-160	V
Collector - Emitter Voltage	V_{CEO}	-150	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\Theta JA}$	625	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E= 0	-160			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B= 0	-150			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C= 0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -120 V , I_E= 0			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -3V , I_C=0			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-1mA			-0.2	V
		I_C= -50 mA, I_B= -5mA			-0.5	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 mA, I_B=-1mA			-1	
		I_C= -50 mA, I_B= -5mA			-1	
DC current gain	$h_{FE(1)}$	V_{CE}= -5V, I_C= -1mA	50			
	$h_{FE(2)}$	V_{CE}= -5V, I_C= -10mA	60		300	
	$h_{FE(3)}$	V_{CE}= -5V, I_C=- 50mA	50			
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz			6	pF
Transition frequency	f_T	V_{CE}= -10V, I_C= -10mA,f=100MHz	100			MHz

■ Marking

Marking	K4M